

SIMULATING THE DYNAMICS OF PARTIAL DISLOCATIONS AND THEIR ASSOCIATED STACKING FAULTS USING THE LEVEL SET METHOD

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ABSTRACT

We have simulated the dynamics of partial dislocations and their associated stacking faults in a face centred cubic (FCC) material using the level set approach. The approach is an extension of that developed by Xiang et al. [1] and Quek et al. [2] for perfect dislocations in bulk and in heteroepitaxial thin film respectively. Incorporating partial dislocations into the level set approach for dislocation dynamics requires additional consideration of constitutive rules associated with the partial dislocations and stacking faults in FCC materials. The equilibrium separation distance of two Shockley partial dislocations calculated using the current approach agrees well with analytical calculations. We also study the behaviour of interacting partial dislocations and their interactions with second phase inclusions in the material. We discuss the feasibility of such a continuum approach to model, in particular, partial dislocations evolution physics.

REFERENCES

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